



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

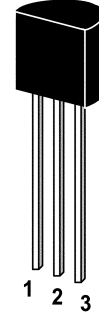
ST 9014

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, A, B, C and D, according to its DC current gain. As complementary type the PNP transistor ST 9015 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



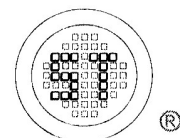
1. Emitter 2. Base 3. Collector

TO-92 Plastic Package

Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	45	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_{C}	100	mA
Power Dissipation	P_{tot}	450	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +150	$^\circ\text{C}$



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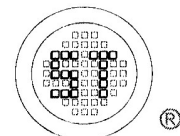
Dated : 07/12/2002

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ST 9014**Characteristics at T_{amb}=25 °C**

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} =5V, I _C =1mA					
Current Gain Group A	h _{FE}	60	-	150	-
B	h _{FE}	100	-	300	-
C	h _{FE}	200	-	600	-
D	h _{FE}	400	-	1000	-
Collector Base Breakdown Voltage at I _C =100μA	V _{(BR)CBO}	50	-	-	V
Collector Emitter Breakdown Voltage at I _C =1mA	V _{(BR)CEO}	45	-	-	V
Emitter Base Breakdown Voltage at I _E =100μA	V _{(BR)EBO}	5	-	-	V
Collector Cutoff Current at V _{CB} =50V	I _{CBO}	-	-	50	nA
Emitter Cutoff Current at V _{EB} =5V	I _{EBO}	-	-	50	nA
Collector Saturation Voltage at I _C =100mA, I _B =5mA	V _{CE(sat)}	-	200	600	mV
Base Saturation Voltage at I _C =100mA, I _B =5mA	V _{BE(sat)}	-	900	-	mV
Gain Bandwidth Product at V _{CE} =5V, I _C =10mA	f _T	-	300	-	MHz
Output Capacitance at V _{CB} =10V, f=1MHz	C _{OB}	-	3.5	6	Pf
Noise Figure at V _{CE} =5V, I _C =200μA f=1KHz, R _G =2KΩ	NF	-	2	10	dB

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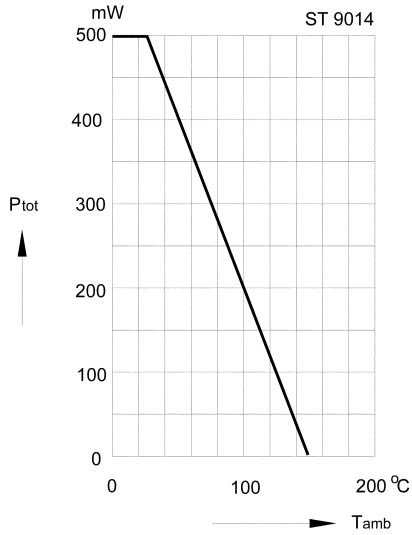
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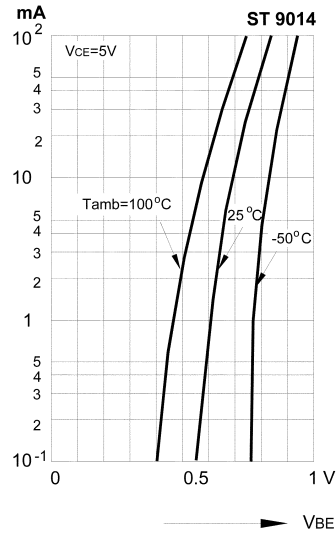
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Admissible power dissipation versus temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

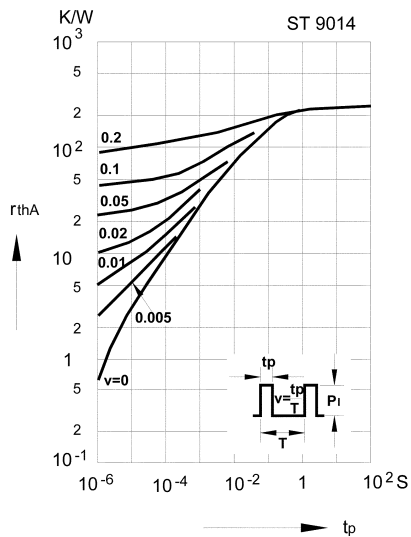


Collector current versus base emitter voltage

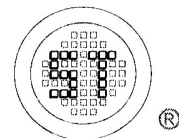
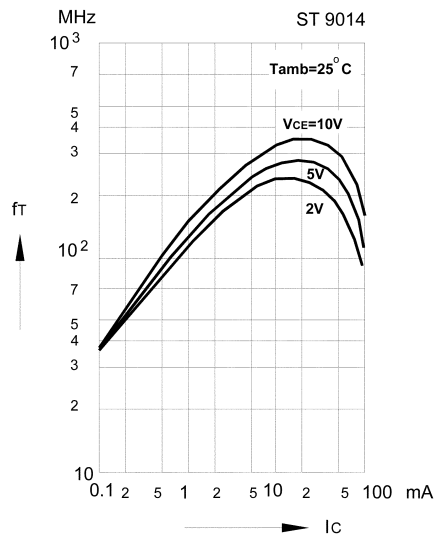


Pulse thermal resistance versus pulse duration

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



Gain bandwidth product versus collector current



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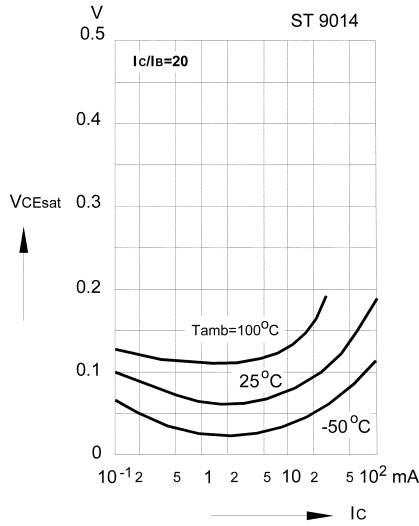
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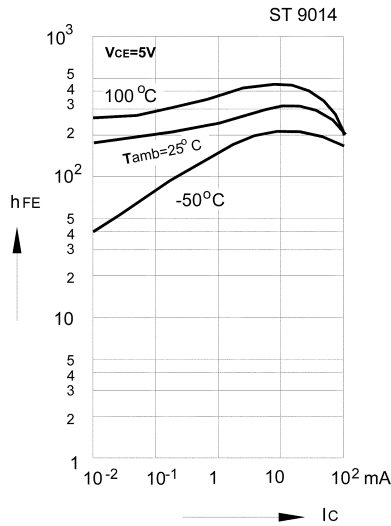
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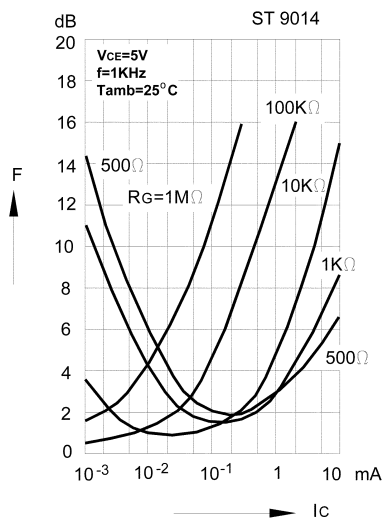
Collector saturation voltage
versus collector current



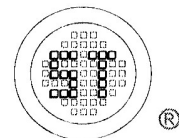
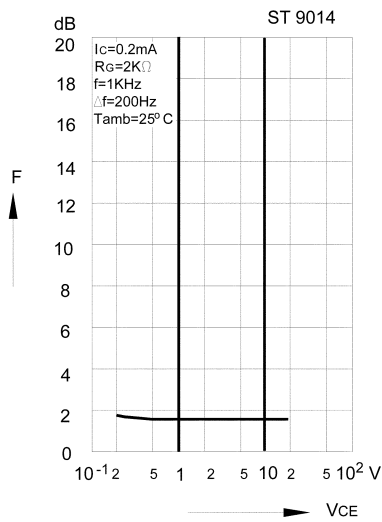
DC current gain
versus collector current



Noise figure
versus collector current



Common emitter
collector characteristics



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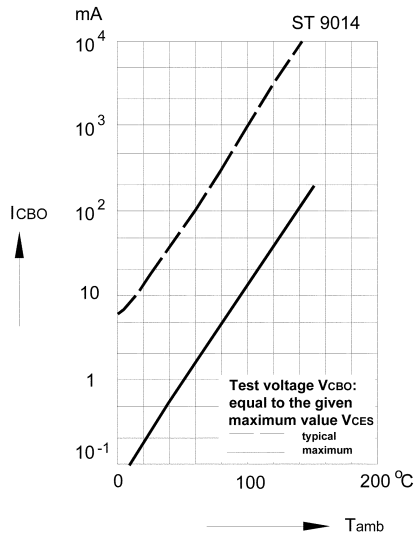
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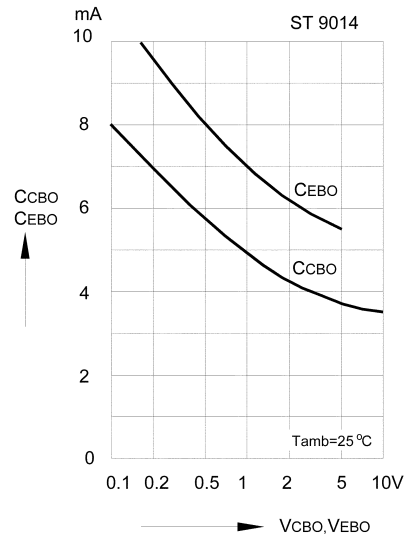
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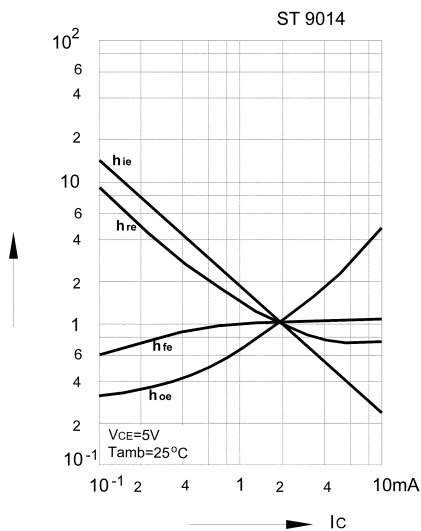
Collector cutoff current versus ambient temperature



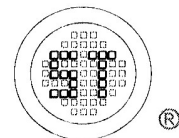
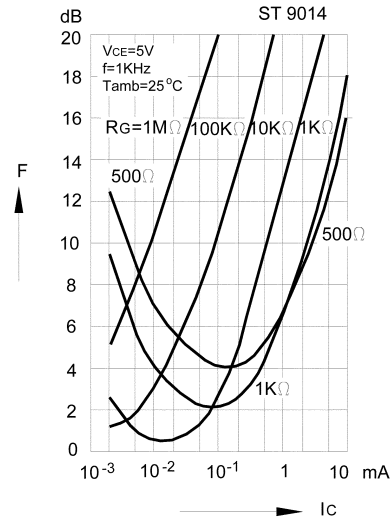
Collector base capacitance, Emitter base capacitance versus reverse bias voltage



Relative h-parameters versus collector current



Noise figure versus collector current



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